TRANSISTOR (PNP) **Plastic-Encapsulate Transistor**

FEATURES

Power dissipation

P_{CM} : 0.2W (Tamb=25°C)

Collector current

I_{CM} : -0.15A

Collector-base Voltage

$V_{(BR)CBO}$: -50 V

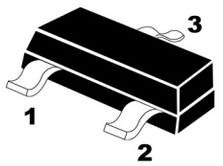
Operating and storage junction temperature range

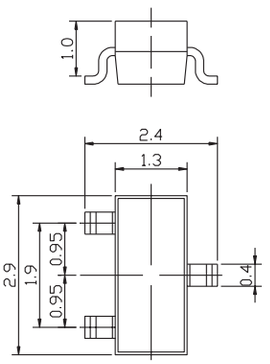
T_J, T_{stg} : -55°C to +150°C

MARKING: A1015LT1=BA

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR





Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100 μA, I_E=0	-50		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-0.1mA, I_B=0	-50		V
Collector cut-off current	I_{CBO}	V_{CB}=-50V, I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0		-0.1	μA
DC current gain	h_{FE}	V_{CE}=-6V, I_C=-2mA	130	400	
Collector-emitter saturation voltage	V_{CEsat}	I_C=-100mA, I_B=-10mA		-0.3	V
Base-emitter saturation voltage	V_{BEsat}	I_C=-100mA, I_B=-10mA		-1.1	V
Base-emitter voltage	V_{BEF}	I_E=-310mA		-1.45	V
Transition frequency	f_r	V_{CE}=-10V, I_C=-1mA,f=30MHz	80		MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	130-200	200-400

RoHS Pb-free TIP Semiconductor